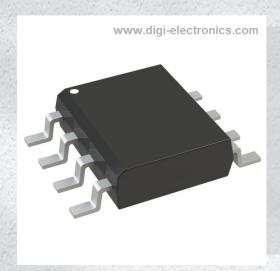


DMG4496SSS-13 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number DMG4496SSS-13-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number DMG4496SSS-13

Description MOSFET N-CH 30V 10A 8SOP

Detailed Description N-Channel 30 V 10A (Ta) 1.42W (Ta) Surface Mount

8-50



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMG4496SSS-13	Diodes Incorporated
Series:	Product Status:
	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	10A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
4.5V, 10V	21.5mOhm @ 10A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
2V @ 250μA	10.2 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±25V	493.5 pF @ 15 V
FET Feature:	Power Dissipation (Max):
	1.42W (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
8-SO	8-SOIC (0.154", 3.90mm Width)
Base Product Number:	
DMG4496	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	





DMG4496SSS

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C	
30V	21.5mΩ @ V _{GS} = 10V	10A	
307	29mΩ @ V _{GS} = 4.5V	8A	

Description

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

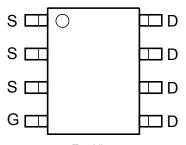
- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

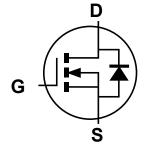
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208 63
- Weight: 0.074 grams (approximate)







Top View Internal Schematic



Equivalent circuit

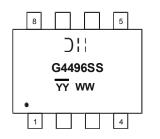
Ordering Information (Note 4 & 5)

Part Number	Compliance	Case	Packaging
DMG4496SSS-13	Standard	SO-8	2500 / Tape & Reel
DMG4496SSSQ-13	Automotive	SO-8	2500 / Tape & Reel

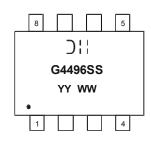
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)





Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6)	Steady State	T _A = +25°C T _A = +85°C	I _D	10 6	А
Pulsed Drain Current (Note 7)			I _{DM}	60	Α
Avalanche Current (Notes 7 & 8)			I _{AR}	8	Α
Repetitive Avalanche Energy (Notes 7 & 8) L = 0.1mH			E _{AR}	3.2	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_{D}	1.42	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	$R_{\theta JA}$	88.49	°C/W
Operating and Storage Temperature Range	T_J , T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

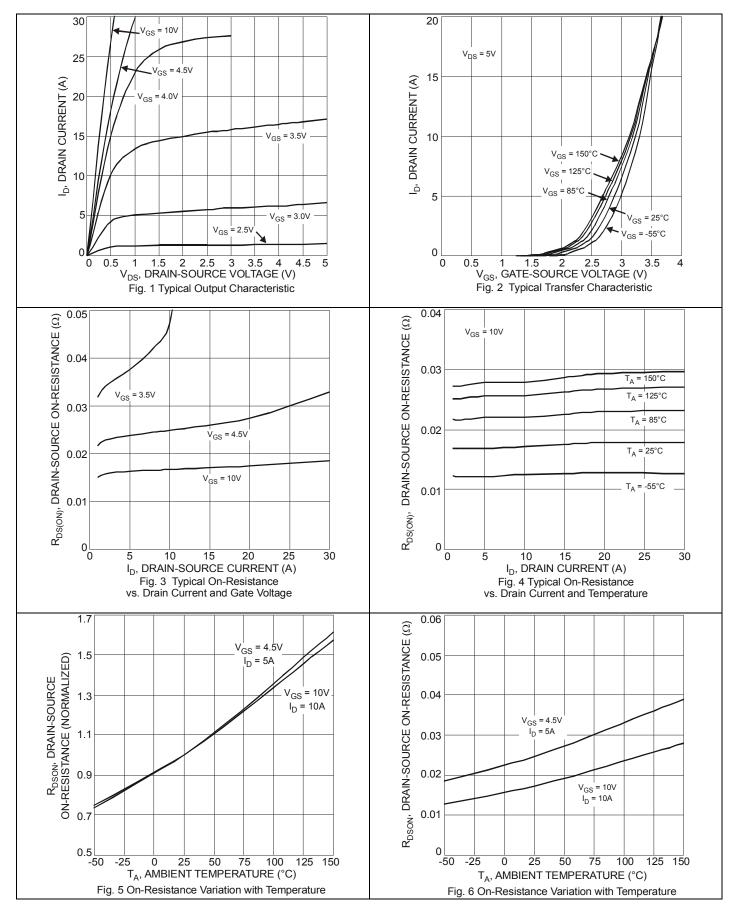
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 30V$, $V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V _{GS} = ±25V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(th)}	0.8	1.2	2.0	٧	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	J		16	21.5	mΩ	V _{GS} = 10V, I _D = 10A
Static Dialif-Source Off-Resistance	R _{DS(ON)}	_	22	29	11122	$V_{GS} = 4.5V, I_D = 7.5A$
Forward Transfer Admittance	Y _{fs}	_	11.7	_	S	V _{DS} = 5V, I _D = 10A
Diode Forward Voltage	V _{SD}	_	0.70	1	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	1	493.5		pF	
Output Capacitance	Coss	_	94.5	_	pF	V _{DS} =15V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	50.4	_	pF 1 - 1:000H2	
Gate Resistance	R_g	_	2.86	_	Ω	V _{DS} =0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	4.7	_	nC	V _{DS} = 15V, V _{GS} = 4.5V, ID =10A
Total Gate Charge (V _{GS} = 10V)	Qg	_	10.2	_	IIC	
Gate-Source Charge	Q _{gs}	_	1.4	_	nC	V _{DS} = 15V, V _{GS} = 10V, ID =10A
Gate-Drain Charge	Q _{gd}	_	1.7	_	nC	
Turn-On Delay Time	t _{D(on)}	_	4.76	_	ns	
Turn-On Rise Time	t _r	_	3.64	_	ns	V _{GS} = 10V, V _{Ds} = 15V,
Turn-Off Delay Time	t _{D(off)}	_	19.5	_	ns $R_G = 6\Omega$, $R_L = 15\Omega$,	
Turn-Off Fall Time	t _f	_	4.9	_	ns	

Notes:

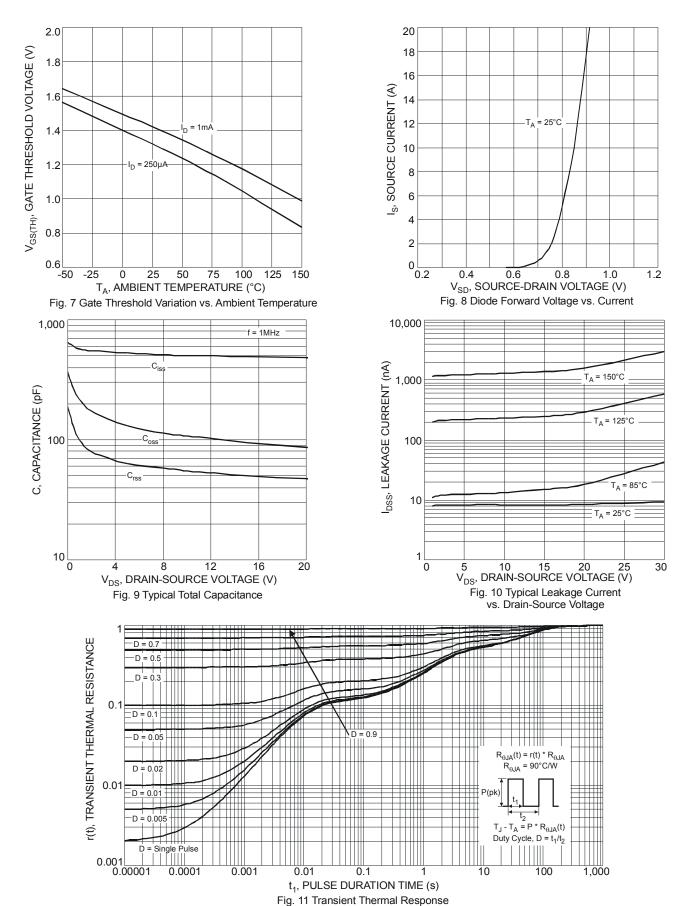
- Device mounted on 1 in.² FR-4 board with 2oz. Copper, in a still air environment @ T_A = +25°C. The value in any given application depends on the user's specific board design.
 Repetitive rating, pulse width limited by junction temperature.
 I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = 25°C
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

- 10. Guaranteed by design. Not subject to production testing.





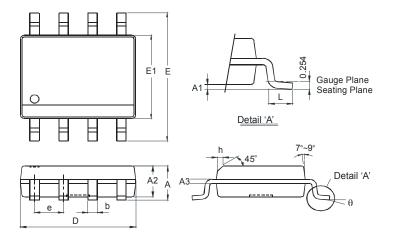






Package Outline Dimensions

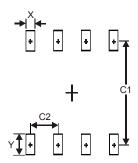
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8				
Dim	Min	Max		
Α	1	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
E	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	-	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27





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